

INTERNATIONAL SCHOOL ON NITRIDE MATERIALS AND DEVICES

17-21 January 2016

Bilkent University, Ankara, Turkey

TOPICS:

New Generation Wide Bandgap

Semiconductors and Nitrides

General Properties of Nitrides:

- Mechanical and Thermal Properties
- Optical Properties
- Defects and Doping

Growth of Nitrides:

- MBE Growth of Nitrides
- MOCVD Growth
- Bulk growth

Band structures

- GaN, InN, AlN and Their Alloys
- Bandgap Engineering of Nitrides

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TOPICS:

Polarization in Nitrides

- Spontaneous Polarization
- Piezoelectric Polarization
- Polarization Engineering

Modeling and Simulation of Nitride
Devices

Optoelectronic Devices in Nitrides

- Nitride LEDs
- Nitride lasers
- New generation nitride solar-cells
- Novel nitride devices

Electron Devices in Nitrides

Low dimensional nitride structures

- Nanowires, Nanorods

To apply, send an e-mail to:

ipek.yayla@bilkent.edu.tr. Graduate students should
attach a letter of recommendation from their advisors..

www.fen.bilkent.edu.tr/~nitrides

